

**IN THE CLAIMS**

Please cancel claims 12-19. The Applicant will pursue these claims in a divisional application.

20. *A method of removing a spin-on compound, comprising:*  
*spin-depositing a spin-on compound on a surface of a substrate, wherein the spin-on compound comprises silicon, wherein the first solvent comprises propyl acetate, and wherein the second solvent comprises ethyl lactate; and*  
*spin-rinsing the spin-on compound with a solvent mixture, wherein the solvent mixture comprises a first solvent that dissolves the spin-on compound, and a second solvent that is inert to the spin-on compound.*
24. (Added) The method of claim 20, wherein the substrate comprises a trench.
25. (Added) The method of claim 24, wherein the spin-on compound is spin-deposited into the trench.
26. (Added) The method of claim 20, wherein the spin-on compound is partially removed.
27. (Added) A method of forming a shallow trench isolation structure, comprising:  
partially removing the spin-on compound according to the method of claim 20 such that an upper surface of the remaining compound is below the surface of the substrate;  
depositing a second compound onto the substrate surface and onto the upper surface of the remaining spin-on compound by chemical vapor deposition.
28. (Added) The method of claim 27, further comprising planarizing the isolation structure such that the surface of the substrate and an upper surface of the second compound are substantially coplanar.

29. (Added) The method of claim 27, wherein the substrate surface and the trench further comprise a thermal oxide coat.
30. (Added) The method of one of claims 20 or 27, wherein the spin-on compound is formed from at least one compound selected from the group consisting of methylsilsesquioxane, hydrogensilsesquioxane, methylhydrosilsesquioxane, silicate, and perhydrosilazane.
31. (Added) The method of claim 27, wherein the second compound is formed from tetraethylorthosilicate or silane.